

MOSFETs Silicon N-channel MOS (U-MOS^{VI}-H)

TK55S10N1

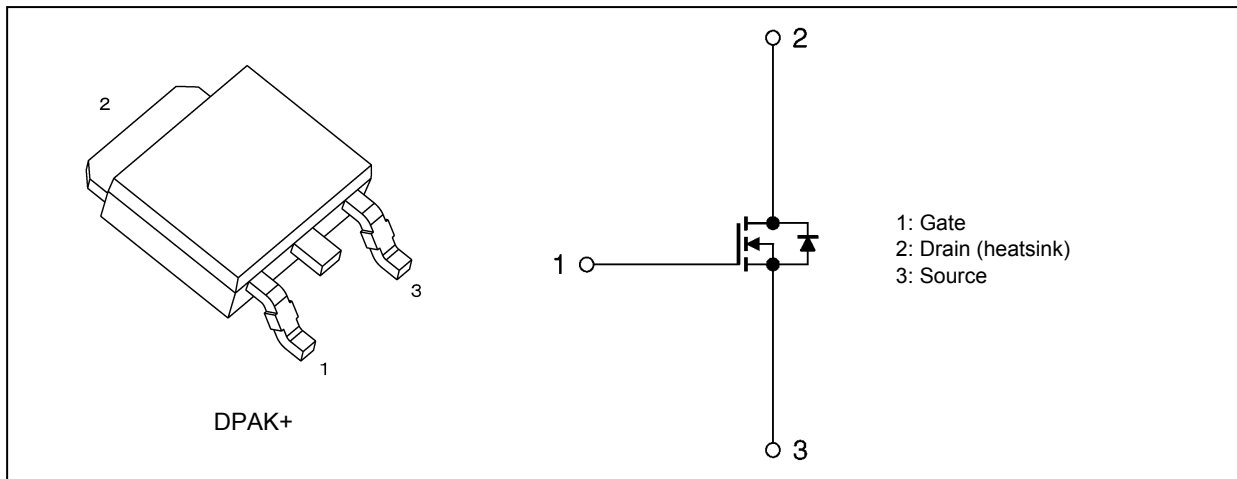
1. Applications

- Automotive
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) AEC-Q101 qualified
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 5.5 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A}$ (max) ($V_{DS} = 100 \text{ V}$)
- (4) Enhancement mode: $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 0.5 \text{ mA}$)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Rating | Unit |
|--------------------------------|---|------------|------------------|
| Drain-source voltage | V_{DSS} | 100 | V |
| Gate-source voltage | V_{GSS} | ± 20 | |
| Drain current (DC) | (Note 1) I_D | 55 | A |
| Drain current (pulsed) | (Note 1) I_{DP} | 165 | |
| Power dissipation | ($T_c = 25^\circ\text{C}$) (Note 2) P_D | 157 | W |
| Single-pulse avalanche energy | (Note 3) E_{AS} | 93 | mJ |
| Single-pulse avalanche current | I_{AS} | 55 | A |
| Channel temperature | (Note 4) T_{ch} | 175 | $^\circ\text{C}$ |
| Storage temperature | (Note 4) T_{stg} | -55 to 175 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2013-02

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|------------------------------------|----------------|------|---------------|
| Channel-to-case thermal resistance | $R_{th(ch-c)}$ | 0.95 | $^{\circ}C/W$ |

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: The power dissipation value is calculated based on the channel-to-case thermal resistance. However, the safe operating area is not only limited to thermal limits but also the current concentration phenomenon. This device should not be used under conditions outside its safe operating area shown herein.

Note 3: $V_{DD} = 80\text{ V}$, $T_{ch} = 25^{\circ}C$ (initial), $L = 24\ \mu H$, $R_G = 25\ \Omega$, $I_{AS} = 55\text{ A}$

Note 4: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---------------|---|-----|------|---------|------------------|
| Gate leakage current | I_{GSS} | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | — | — | ± 1 | μA |
| Drain cut-off current | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | — | — | 10 | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$ | 100 | — | — | V |
| Drain-source breakdown voltage (Note 5) | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$ | 65 | — | — | |
| Gate threshold voltage | V_{th} | $V_{DS} = 10\text{ V}, I_D = 0.5\text{ mA}$ | 2.0 | — | 4.0 | |
| Drain-source on-resistance | $R_{DS(ON)}$ | $V_{GS} = 10\text{ V}, I_D = 27.5\text{ A}$ | — | 5.5 | 6.5 | $\text{m}\Omega$ |

Note 5: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------|-----------|---|-----|------|-----|-------------|
| Input capacitance | C_{iss} | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | — | 3280 | — | pF |
| Reverse transfer capacitance | C_{rss} | | — | 210 | — | |
| Output capacitance | C_{oss} | | — | 1520 | — | |
| Switching time (rise time) | t_r | See Figure 6.2.1. | — | 11 | — | ns |
| Switching time (turn-on time) | t_{on} | | — | 28 | — | |
| Switching time (fall time) | t_f | | — | 19 | — | |
| Switching time (turn-off time) | t_{off} | | — | 51 | — | |

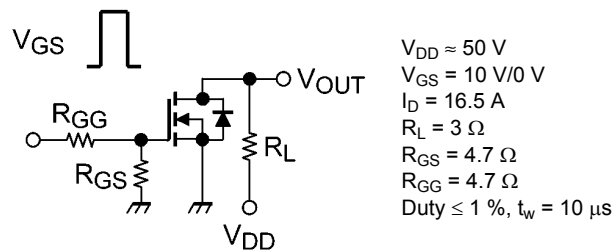


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|-----------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_g | $V_{DD} \approx 80\text{ V}, V_{GS} = 10\text{ V}, I_D = 55\text{ A}$ | — | 49 | — | nC |
| Gate-source charge 1 | Q_{gs1} | | — | 15 | — | |
| Gate-drain charge | Q_{gd} | | — | 14 | — | |

6.4. Source-Drain Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|-----------|--|-----|------|------|------|
| Reverse drain current (DC) (Note 6) | I_{DR} | — | — | — | 55 | A |
| Reverse drain current (pulsed) (Note 6) | I_{DRP} | | — | — | 165 | |
| Diode forward voltage | V_{DSF} | $I_{DR} = 55\text{ A}, V_{GS} = 0\text{ V}$ | — | — | -1.2 | V |
| Reverse recovery time (Note 7) | t_{rr} | $I_{DR} = 55\text{ A}, V_{GS} = 0\text{ V}$ $-di_{DR}/dt = 50\text{ A}/\mu\text{s}$ | — | 75 | — | ns |
| Reverse recovery charge (Note 7) | Q_{rr} | | — | 73 | — | |

Note 6: Ensure that the channel temperature does not exceed 175°C .

Note 7: Ensure that V_{DS} peak does not exceed V_{DSS} .

7. Marking (Note)

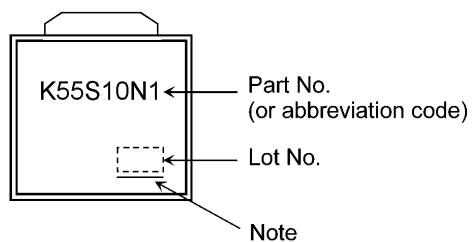


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

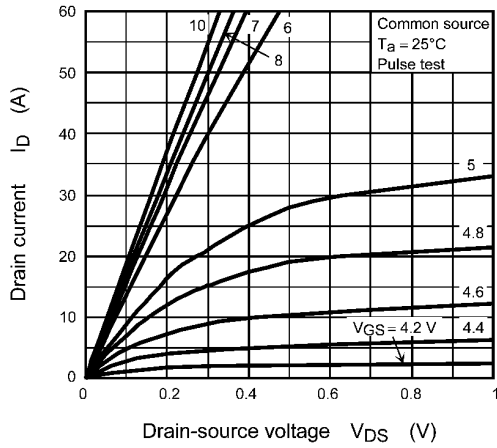


Fig. 8.1 $I_D - V_{DS}$

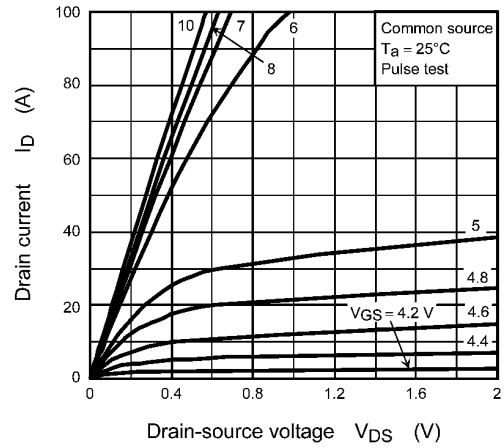


Fig. 8.2 $I_D - V_{DS}$

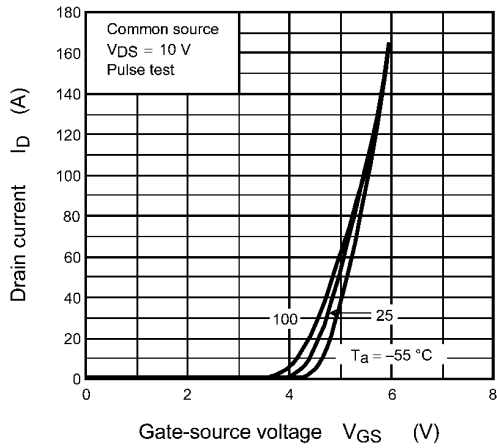


Fig. 8.3 $I_D - V_{GS}$

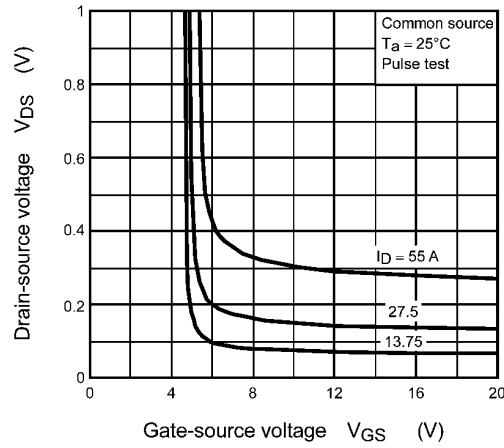


Fig. 8.4 $V_{DS} - V_{GS}$

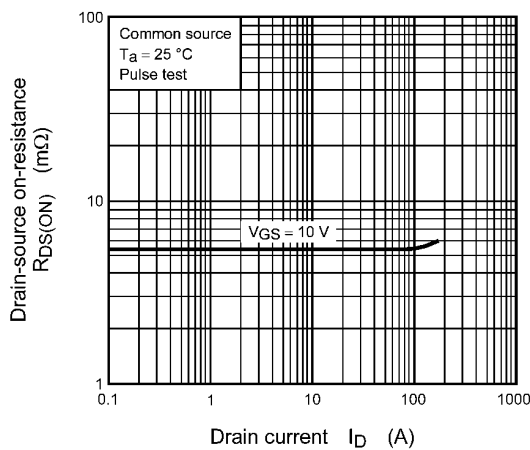


Fig. 8.5 $R_{DS(ON)} - I_D$

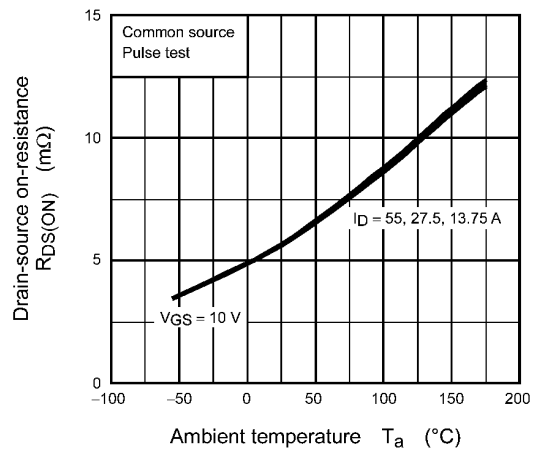


Fig. 8.6 $R_{DS(ON)} - T_a$

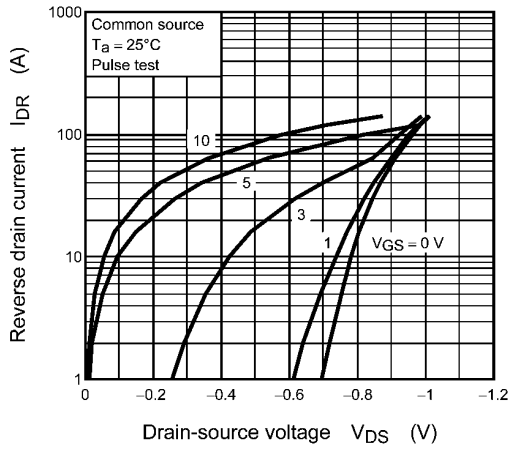


Fig. 8.7 $I_{DR} - V_{DS}$

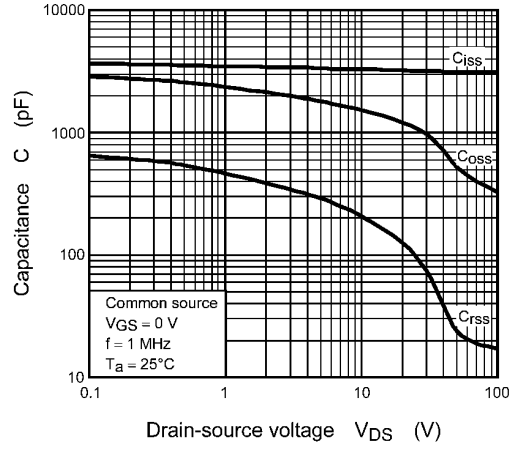


Fig. 8.8 Capacitance - V_{DS}

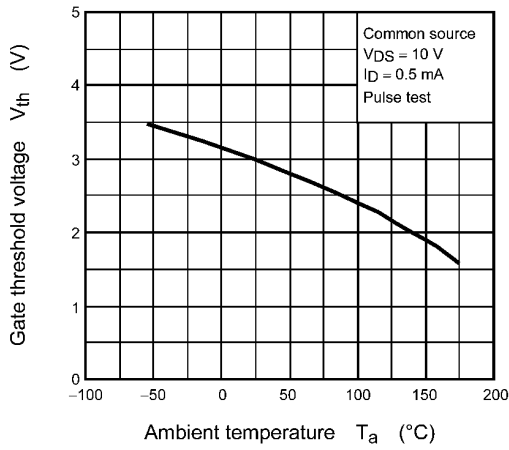


Fig. 8.9 $V_{th} - T_a$

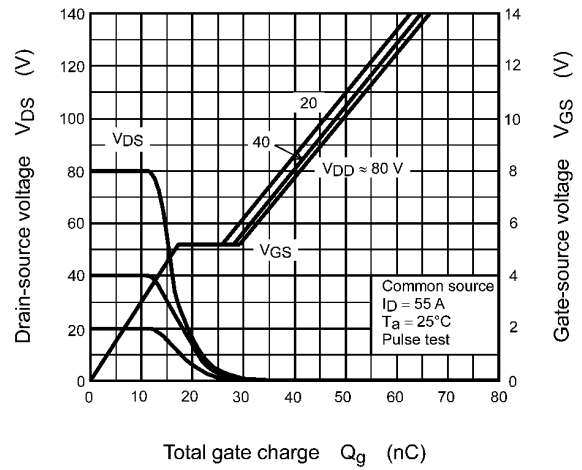


Fig. 8.10 Dynamic Input/Output Characteristics

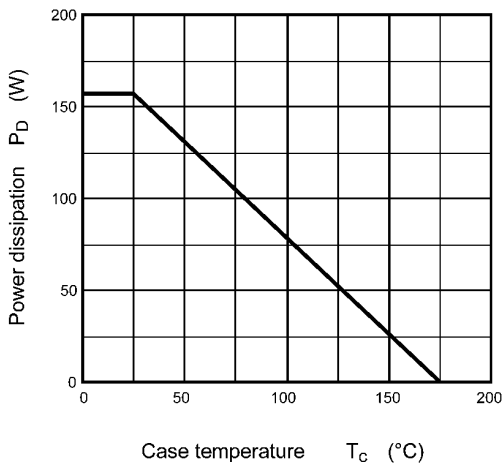


Fig. 8.11 $P_D - T_c$
 (Guaranteed Maximum)

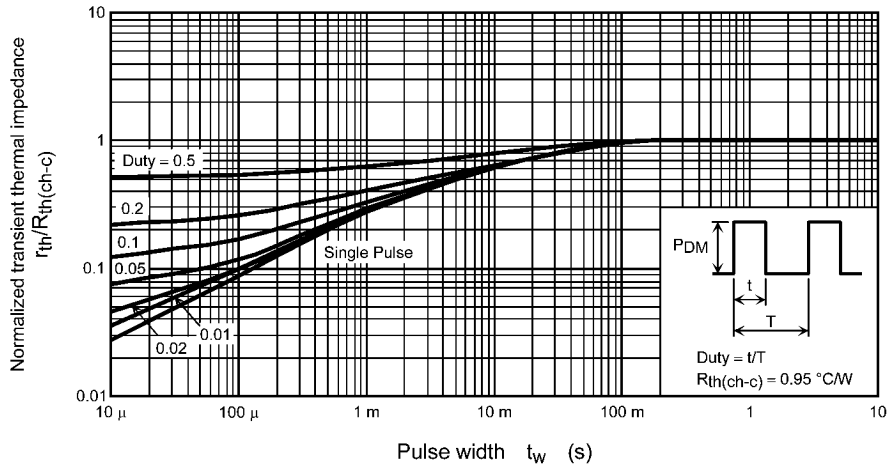


Fig. 8.12 $r_{th}/R_{th(ch-c)} - t_w$
(Guaranteed Maximum)

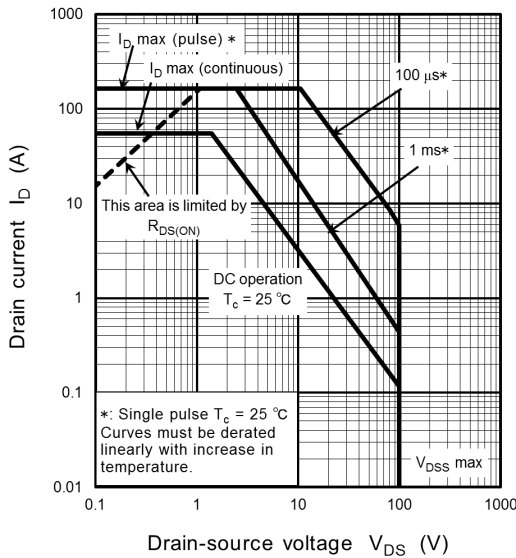


Fig. 8.13 Safe Operating Area
(Guaranteed Maximum)

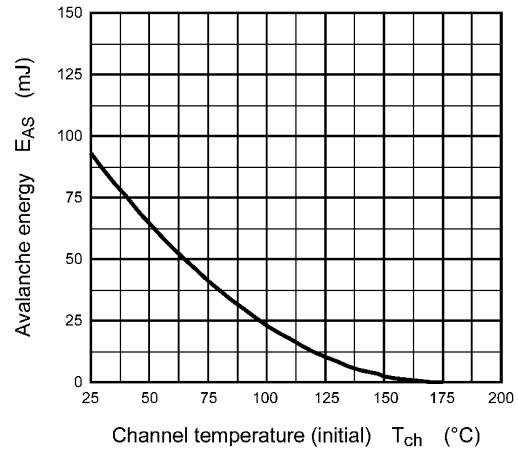
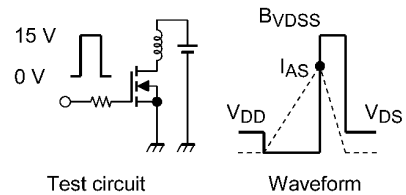


Fig. 8.14 $E_{AS} - T_{ch}$
(Guaranteed Maximum)



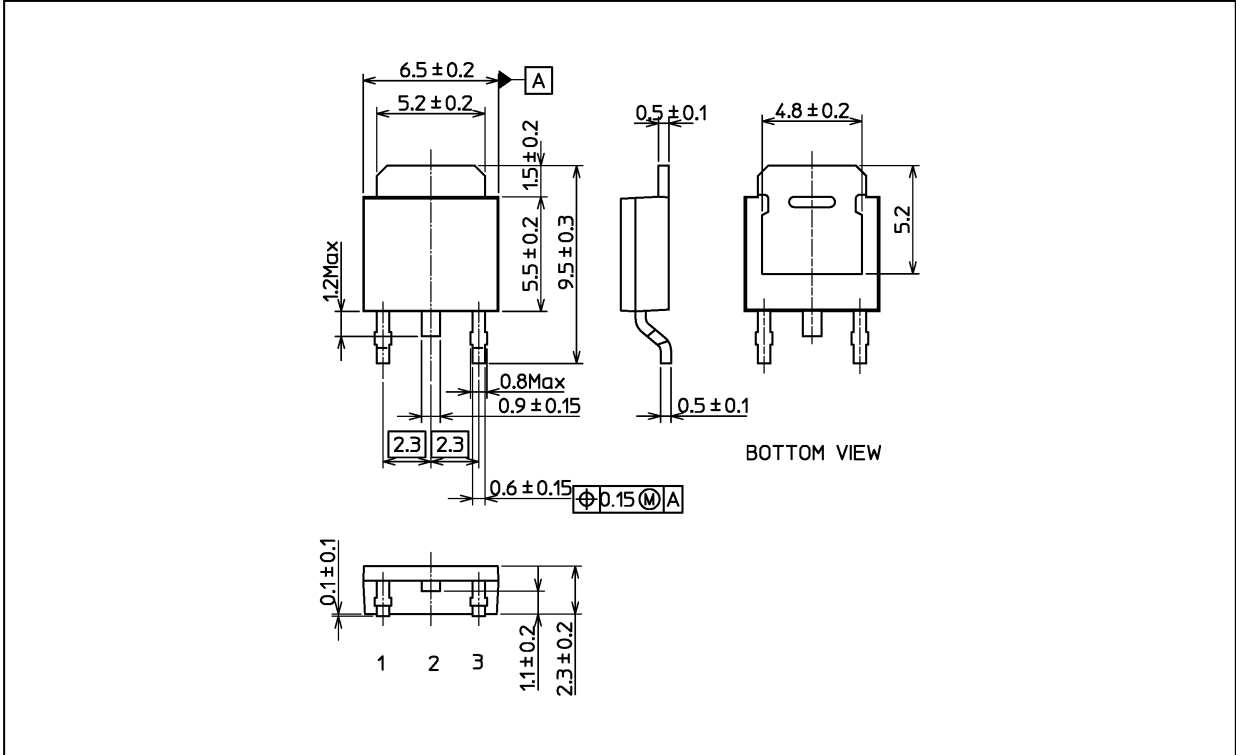
$$R_G = 25 \Omega \quad V_{DD} = 80 \text{ V}, L = 24 \mu\text{H} \quad E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

Fig. 8.15 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

| Package Name(s) |
|-----------------|
| TOSHIBA: 2-7M1A |
| Nickname: DPAK+ |

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